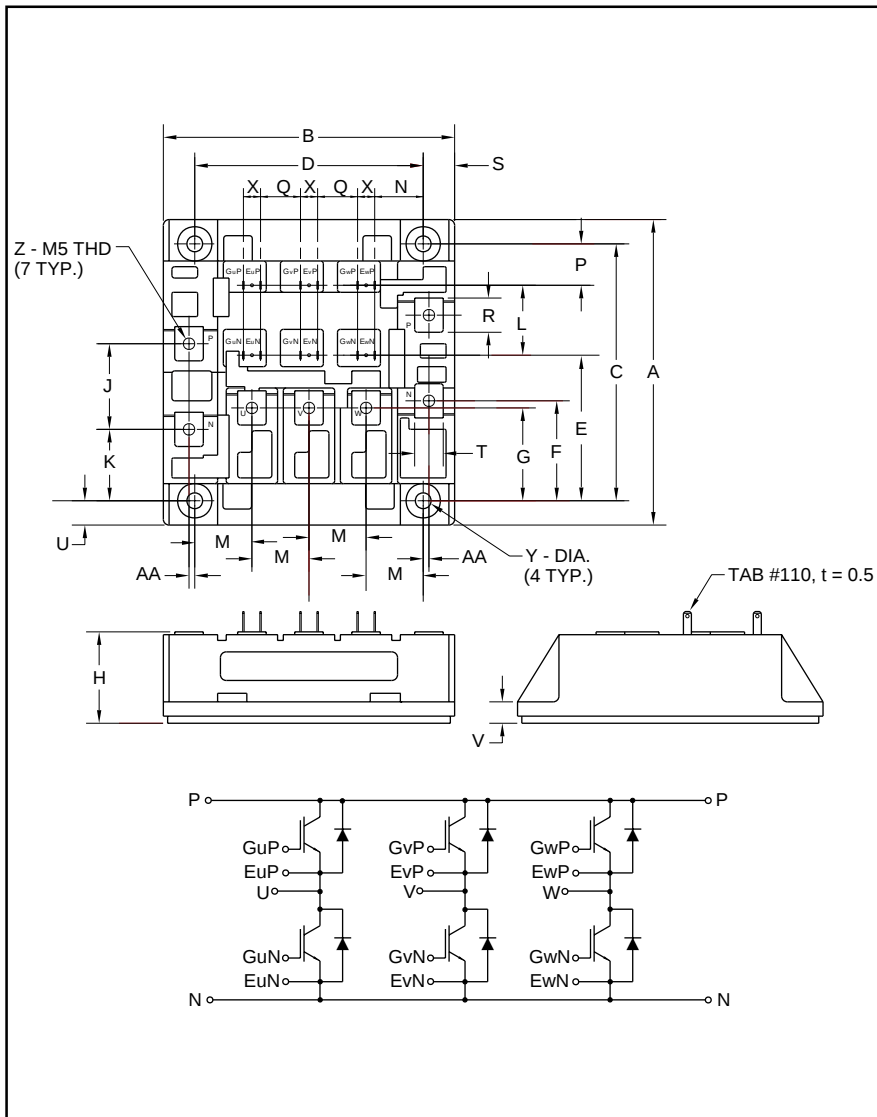


MITSUBISHI IGBT MODULES
CM100TF-24H
 HIGH POWER SWITCHING USE
 INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	4.02	102.0
C	3.543±0.01	90.0±0.25
D	3.15±0.01	80.0±0.25
E	2.01	51.0
F	1.38	35.0
G	1.28	32.5
H	1.26 Max.	32.0 Max
J	1.18	30.0
K	0.98	25.0
L	0.96	24.5
M	0.79	20.0
N	0.67	17.0

Dimensions	Inches	Millimeters
P	0.57	14.5
Q	0.55	14.0
R	0.47	12.0
S	0.43	11.0
T	0.39	10.0
U	0.33	8.5
V	0.30	7.5
X	0.24	6.0
Y	0.22	5.5
Z	M5 Metric	M5
AA	0.08	2.0



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM100TF-24H is a 1200V (V_{CES}), 100 Ampere Six-IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	100	24

CM100TF-24H**HIGH POWER SWITCHING USE
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Ratings	Symbol	CM100TF-24H	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_C = 25^\circ\text{C}$)	I_C	100	Amperes
Peak Collector Current	I_{CM}	200*	Amperes
Emitter Current** ($T_C = 25^\circ\text{C}$)	I_E	100	Amperes
Peak Emitter Current**	I_{EM}	200*	Amperes
Maximum Collector Dissipation ($T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)	P_C	780	Watts
Mounting Torque, M5 Main Terminal	—	1.47 ~ 1.96	$\text{N} \cdot \text{m}$
Mounting Torque, M5 Mounting	—	1.47 ~ 1.96	$\text{N} \cdot \text{m}$
Weight	—	830	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	V_{rms}

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDI).

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}$, $V_{\text{GE}} = 0\text{V}$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}$, $V_{\text{CE}} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 10\text{mA}$, $V_{\text{CE}} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 100\text{A}$, $V_{\text{GE}} = 15\text{V}$	—	2.5	3.4**	Volts
		$I_C = 100\text{A}$, $V_{\text{GE}} = 15\text{V}$, $T_j = 150^\circ\text{C}$	—	2.25	—	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 600\text{V}$, $I_C = 100\text{A}$, $V_{\text{GE}} = 15\text{V}$	—	500	—	nC
Emitter-Collector Voltage	V_{EC}	$I_E = 100\text{A}$, $V_{\text{GE}} = 0\text{V}$	—	—	3.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{\text{GE}} = 0\text{V}$, $V_{\text{CE}} = 10\text{V}$	—	—	20	nF
Output Capacitance	C_{oes}		—	—	7	nF
Reverse Transfer Capacitance	C_{res}		—	—	4	nF
Resistive	Turn-on Delay Time	$V_{\text{CC}} = 600\text{V}$, $I_C = 100\text{A}$, $V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}$, $R_G = 3.1\Omega$	—	—	250	ns
Load	Rise Time		—	—	350	ns
Switching	Turn-off Delay Time		—	—	300	ns
Times	Fall Time		—	—	350	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 100\text{A}$, $di_E/dt = -200\text{A}/\mu\text{s}$	—	—	250	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 100\text{A}$, $di_E/dt = -200\text{A}/\mu\text{s}$	—	0.74	—	μC

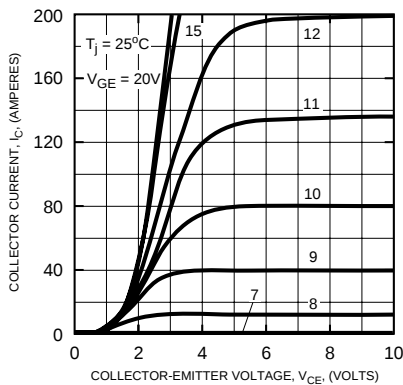
Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per IGBT	—	—	0.16	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per FWDI	—	—	0.35	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	—	—	0.025	$^\circ\text{C}/\text{W}$

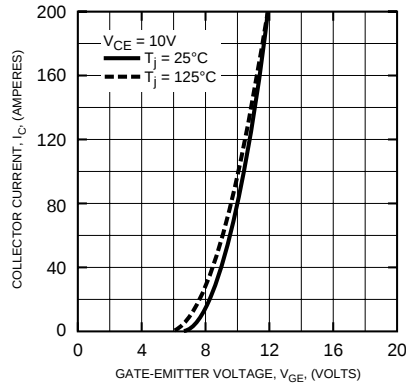
CM100TF-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

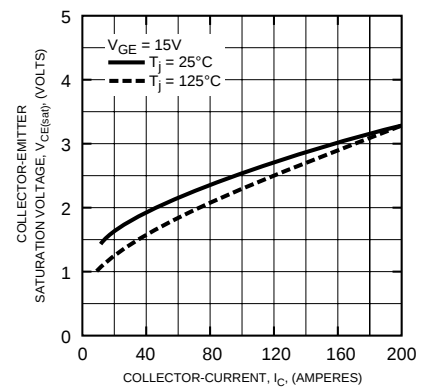
OUTPUT CHARACTERISTICS
(TYPICAL)



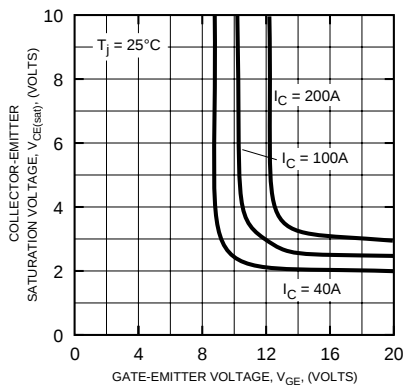
TRANSFER CHARACTERISTICS
(TYPICAL)



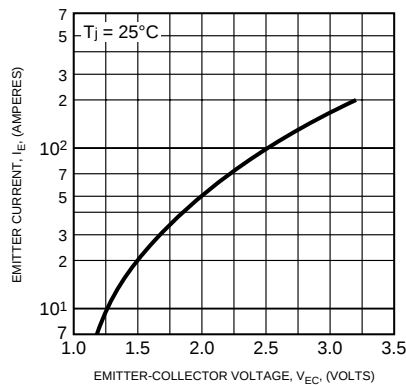
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



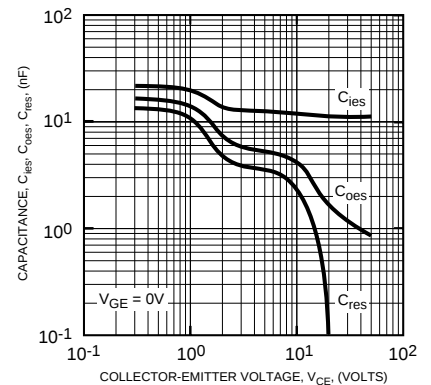
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



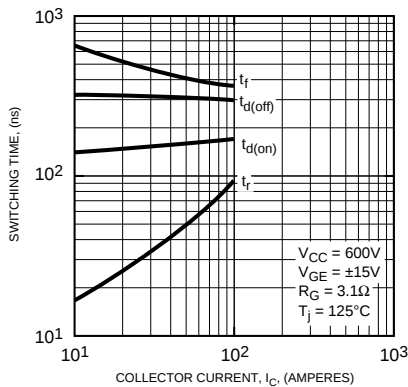
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



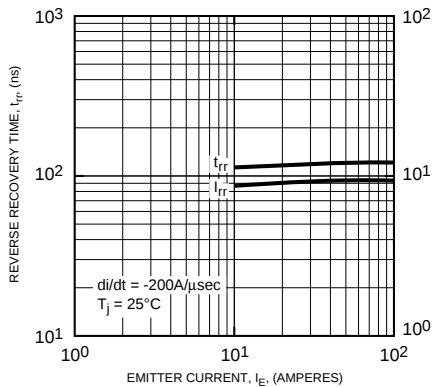
CAPACITANCE VS. V_{CE}
(TYPICAL)



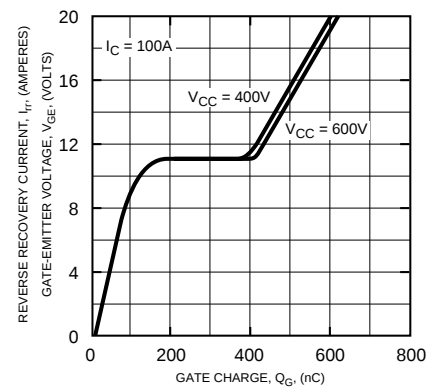
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, V_{GE}



CM100TF-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

